

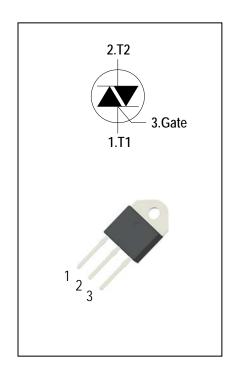
3 Quadrants High temperature Triacs

General Description

High current density due to mesa technology , guaranteed maximum junction temperature 150° C. The AIS30CH triac series is suitable for general purpose AC switching. They can beused as an ON/OFF function in applications such as static relays, heating regulation, High power motor controls e.g. washing machines and vacuum cleaners,Rectifier-fed DC inductive loads e.g.DC motors and solenoids , motor speed controllers. The heatsink can be reduced,compared to traditional triacs, according to the high performance at given junction temperatures.

Features

- ◆ Repetitive Peak Off-State Voltage: 600V/800V
- ◆ R.M.S On-State Current (IT(RMS)= 30A)
- ♦ High Commutation dv/dt
- High junction temperature operating capability
- ◆ These Devices are Pb-Free and are RoHS Compliant
- ◆ Isolated heatsink mounted , Isolation Voltage (Viso = 2500V AC)



Absolute Maximum Ratings

Symbol	Items	Conditions		Ratings	Unit
V_{DRM}	Depotitive Deals Off State Voltage	Ti = 25°C	AIS30CH60H	600	V
V_{RRM}	Repetitive Peak Off-State Voltage	Tj = 25°C	AIS30CH80H	800	V
I _{T(RMS)}	R.M.S On-State Current	T _C = 95°C		30	Α
I _{TSM}	Surge On-State Current	tp=20ms(50Hz)/tp=16.7ms(60Hz)		270/285	А
l ² t	I ² t for fusing	tp=10ms		488	A ² s
-11/-14	Critical rate of rise of on-state	ritical rate of rise of on-state F = 120 Hz Tj = 150°C		50	A/µs
dl/dt	current	$I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$			
I _{GM}	Peak Gate Current	tp = 20 μs Tj = 150°C		4	А
$P_{G(AV)}$	Average Gate Power Dissipation(Tj=150°C)			1	W
P_GM	Peak Gate Power Dissipation(tp=20us,Tj=150°C)			10	W
T _j	Operating Junction Temperature			- 40 ~ 150	°C
T _{STG}	Storage Temperature			- 40 ~ 150	°C



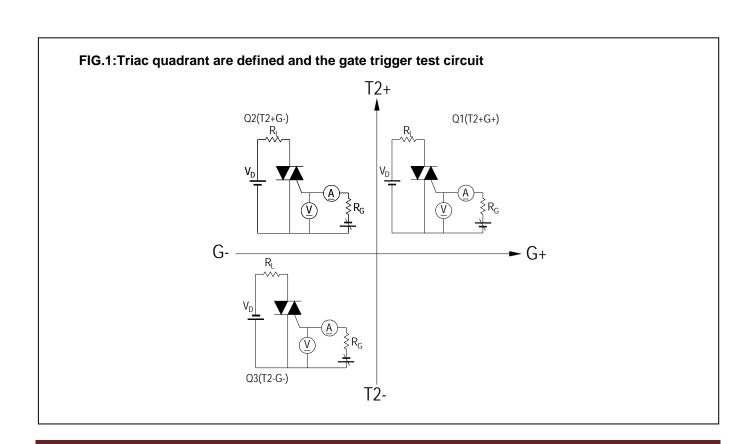


1 / 6 www.advsemi.com Feb,2013 -Rev.3.02



Electrical Characteristics(Tj = 25°C unless otherwise specified)

Symbol	Items		Conditions		AIS30CH60H/80H		80H	Unit
					S	Blank	В	
I _{DRM}	Peak Forward Reverse Blocking		$V_{DRM} = V_{RRM}$, $Tj = 25$ °C	May	10		uA	
I _{RRM}	Current		$V_{DRM} = V_{RRM}$, $Tj = 150$ °C	Max.	8.5		mA	
V _{TM}	Peak On-S	tate Voltage	I _{TM} = 42A, t _p = 380 μs	Max.	1.5			٧
V_{GD}	Q1-Q2-Q3	Non-Trigger Gate Voltage	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $Tj = 150^{\circ}\text{C}$	Min.	0.15		V	
V_{GT}	Q1-Q2-Q3	Gate Trigger Voltage	Max.		1.3		V	
I _{GT}	Q1-Q2-Q3	Gate Trigger Current	$V_D = 12V$, $R_L = 33\Omega$	Max.	10	35	50	mA
I _H	Q1-Q2-Q3	Holding Current	I _T = 0.1A	Max.	20	50	75	mA
ΙL	Q1-Q3	Latching Current	I _G = 1.2 I _{GT}	Max.	20	80	90	mA
	Q2				35	90	110	
dV/dt	Critical Rate of Rise of Off-State Voltage		$V_D = 2/3V_{DRM}$ gate open Tj = 150°C	Min.	500	1000	1500	V/µs
(dV/dt)c	Critical Rate of Change of Commutating Voltage		V _D =400V Tj = 150°C (dI/dt)c=-16A/ms	Min.	1	15	20	V/µs
R _{th(j-c)}	Junction to case (AC)			Max.	0.9			°C/W
R _{th(j-a)}	Junction to ambient			Max.	50			°C/W



ADV

FIG.2: Maximum on-state power dissipation

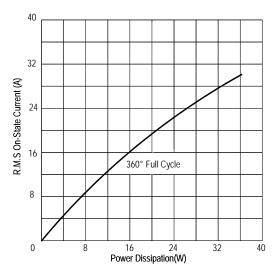


FIG.4: Maximum transient thermal impedance

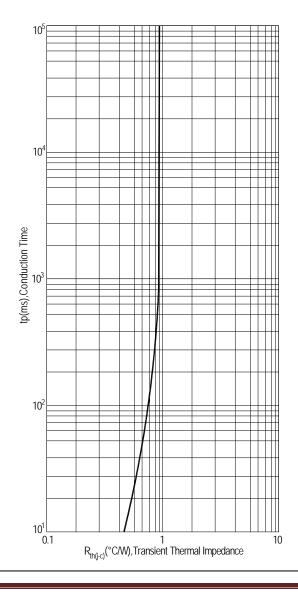


FIG.3: Typical RMS on-state current VS Allowable case Temperature

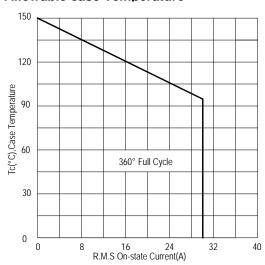


FIG.5: Rated surge on-state current (Non-Repetitive)

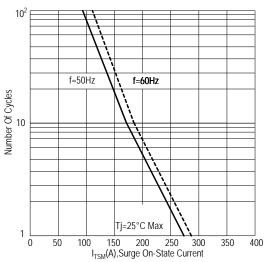


FIG.6: Gate trigger current VS Junction temperature

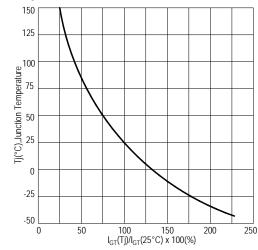




FIG.7:Holding current and Latching current VS Junction temperature

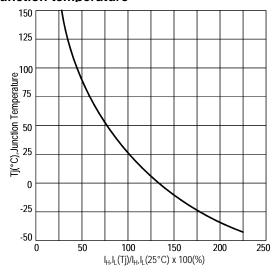


FIG.8: Gate trigger voltage VS Junction temperature

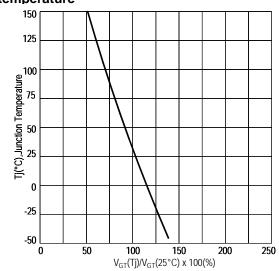
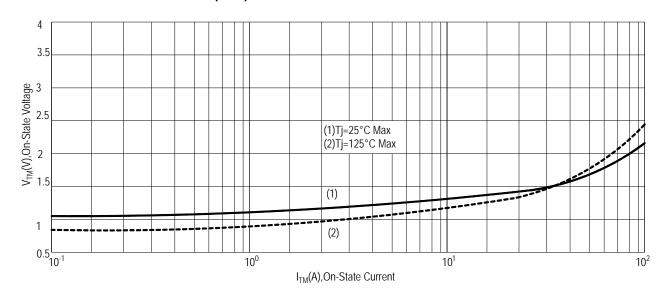


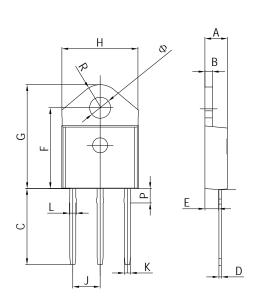
FIG.9: On-state characteristics(Max)



4 / 6 www.advsemi.com Feb,2013 -Rev.3.02

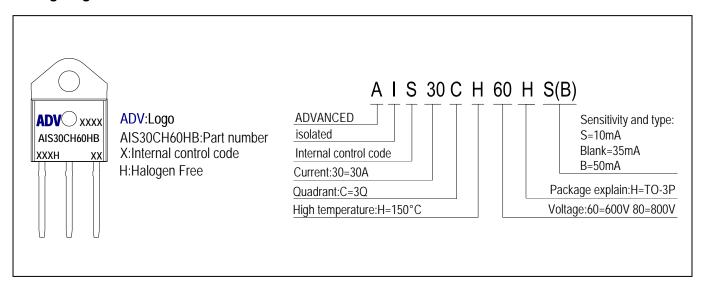


PACKAGE MECHANICAL DATA TO-3P(isolated) Package Dimension



	Dimensions In		Dimensions In		
Symbol	Millimeters		Inches		
	Min	Max	Min	Max	
Α	4.4	4.6	0.173	0.181	
В	1.45	1.55	0.057	0.061	
С	14.35	15.60	0.565	0.614	
D	0.5	0.7	0.020	0.028	
Е	2.7	2.9	0.106	0.114	
F	15.8	16.5	0.622	0.650	
G	20.4	21.1	0.815	0.831	
Н	15.1	15.5	0.594	0.610	
J	5.4	5.65	0.213	0.222	
K	1.2	1.4	0.047	0.055	
Ø	4.08	4.20	0.161	0.165	
L	1.35	1.50	0.053	0.059	
Р	2.8	3.0	0.110	0.118	
R	4.60 typ.		0.181 typ.		

Making Diagram



Ordering information

Part number	Package	Marking	Packing	Quantity		
AIS30CH60H#	TO-3P isolated	AIS30CH60H#	Tube	30pcs		
AIS30CH80H#	TO-3P isolated	AIS30CH80H#	Tube	30pcs		
Note:# = Gate Trigger Current Sensitivity and type						



AIS30CH60H/80H

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6 / 6 www.advsemi.com Feb,2013 -Rev.3.02